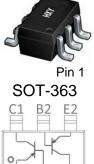


#### **FEATURES**

Epitaxial planar die construction. Ideal for low power amplification and switching.

## Package Marking and Ordering Information

| Product ID | Pack    | Marking | Qty(PCS) |
|------------|---------|---------|----------|
| MMDT3906   | SOT-363 | K3N     | 3000     |



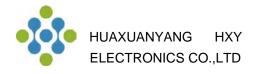
## MAXIMUM RATINGS (Ta=25 unless otherwise noted)

| MAXIMUN                          | I RATINGS (Ta=25 unless otherwise not            | ted)     | Pin 1 |  |
|----------------------------------|--|----------|-------|--|
| Symbol                           | Parameter  | Value    | Unit  |  |
| V <sub>CBO</sub>                 | Collector-Base Voltage                           | -40      | V     |  |
| V <sub>CEO</sub>                 | Collector-Emitter Voltage                        | -40      | V     |  |
| V <sub>EBO</sub>                 | Emitter-Base Voltage                             | -5       | V     |  |
| lc                               | Collector Current                                | -200     | mA    |  |
| Pc                               | Collector Power Dissipation                      | 200      | mW    |  |
| R <sub>ØJA</sub>                 | Thermal Resistance From Junction To Ambient      | 625      | °C/W  |  |
| T <sub>J</sub> ,T <sub>stg</sub> | Operation Junction And Storage Temperature Range | -55~+150 | °C    |  |

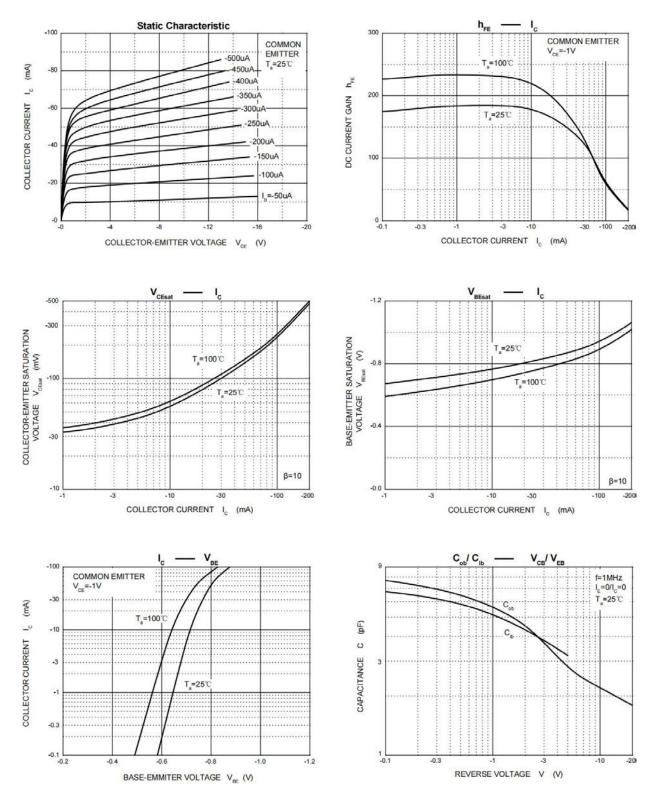
## ELECTRICAL CHARACTERISTICS(Ta=25 unless otherwise noted)

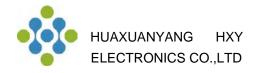
| Symbol                   | Parameter Test conditions   |   | Min   | Тур | Max   | Unit |
|--------------------------|---|---|-------|-----|-------|------|
| V <sub>(BR)CBO</sub> *   | Collector-base breakdown voltage                                  | I <sub>C</sub> =-10μΑ, I <sub>E</sub> =0                      | -40   |     |       | V    |
| V <sub>(BR)CEO</sub> *   | Collector-emitter breakdown voltage                               | I <sub>C</sub> =-1mA, I <sub>B</sub> =0 -40                   |       |     |       | V    |
| V <sub>(BR)EBO</sub> *   | Emitter-base breakdown voltage                                    | I <sub>E</sub> =-10μA, I <sub>C</sub> =0 -5                   |       |     |       | V    |
| I <sub>CEX</sub> *       | Collector cut-off current   | V <sub>CE</sub> =-30V, V <sub>EB(off)</sub> =-3V              |       |     | -50   | nA   |
| I <sub>CBO</sub>         | Collector cut-off current   | V <sub>CB</sub> =-40V, I <sub>E</sub> =0                      |       |     | -100  | nA   |
| I <sub>EBO</sub>         | Base cut-off current  | V <sub>EB</sub> =-5V,I <sub>E</sub> =0                        |       |     | -50   | nA   |
| h <sub>FE</sub> (1)*     | DC current gain(1)  | V <sub>CE</sub> =-1V, I <sub>C</sub> =-100 µ A                | 60    |     |       |      |
| h <sub>FE</sub> (2)*     | 2)* DC current gain(2) V <sub>CE</sub> =-1V, I <sub>C</sub> =-1mA |   | 80    |     |       |      |
| h <sub>FE</sub> (3)*     | * DC current gain(3) V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA  |   | 100   |     | 300   |      |
| h <sub>FE</sub> (4)*     | DC current gain(4)  | V <sub>CE</sub> =-1V, I <sub>C</sub> =-50mA                   |       |     |       |      |
| h <sub>FE</sub> (5)*     | DC current gain(5)  | V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA                  | 30    |     |       |      |
| \/ *                     |   | I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA                   |       |     | -0.25 | V    |
| V <sub>CE(sat)</sub> *   | Collector-emitter saturation voltage                              | I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA                   |       |     | -0.4  | V    |
| \/ <b>*</b>              |   | I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA                   | -0.65 |     | -0.85 | V    |
| V <sub>BE(sat)</sub> *   | Base-emitter saturation voltage                                   | I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA                   |       |     | -0.95 | V    |
| f⊤                       | Transition frequency  | V <sub>CE</sub> =-20V, I <sub>C</sub> =-10mA, f=100MHz        | 250   |     |       | MHz  |
| Cob                      | Collector output capacitance                                      | V <sub>CB</sub> =-5V, I <sub>E</sub> =0, f=1MHz               |       |     | 4.5   | pF   |
| NF                       | Noise figure  | VCE=-5V,Ic=-0.1mA,f=1kHz,Rg=1KΩ                               |       |     | 4     | dB   |
| t <sub>d</sub>           | Delay time  | V <sub>CC</sub> =-3V, V <sub>BE(off)</sub> =-0.5V,            |       |     | 35    | ns   |
| tr                       | Rise time   | I <sub>C</sub> =-10mA, I <sub>B1</sub> =I <sub>B2</sub> =-1mA |       |     | 35    | ns   |
| ts                       | Storage time  | V <sub>cc</sub> =-3V, I <sub>c</sub> =-10mA,                  |       |     | 225   | ns   |
| t <sub>f</sub> Fall time |   | I <sub>B1</sub> =I <sub>B2</sub> =-1mA                        |       |     | 75    | ns   |

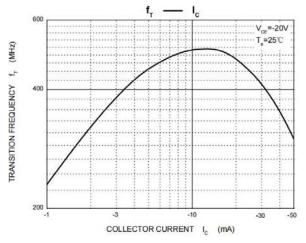
\*Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

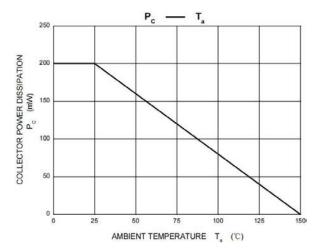


# **Typical Characteristics**

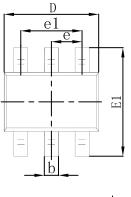


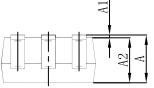


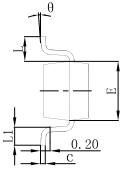




## **SOT-363 Package Outline Dimensions**

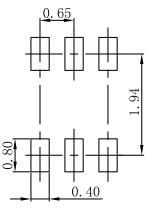






| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |  |
|--------|---------------------------|-------|----------------------|-------|--|
| Symbol | Min                       | Max   | Min                  | Max   |  |
| A      | 0.900                     | 1.100 | 0.035                | 0.043 |  |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |  |
| A2     | 0.900                     | 1.000 | 0.035                | 0.039 |  |
| b      | 0.150                     | 0.350 | 0.006                | 0.014 |  |
| С      | 0.100                     | 0.150 | 0.004                | 0.006 |  |
| D      | 2.000                     | 2.200 | 0.079                | 0.087 |  |
| E      | 1.150                     | 1.350 | 0.045                | 0.053 |  |
| E1     | 2.150                     | 2.400 | 0.085                | 0.094 |  |
| е      | 0.650 TYP                 |       | 0.026 TYP            |       |  |
| e1     | 1.200                     | 1.400 | 0.047                | 0.055 |  |
| L      | 0.525 REF                 |       | 0.021 REF            |       |  |
| L1     | 0.260                     | 0.460 | 0.010                | 0.018 |  |
| θ      | 0°                        | 8°    | 0°                   | 8°    |  |

## SOT-363 Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.



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